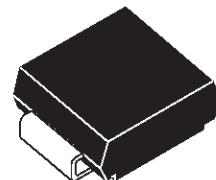


FAST RECOVERY RECTIFIER DIODES

FEATURES

- VERY LOW REVERSE RECOVERY TIME
- VERY LOW SWITCHING LOSSES
- LOW NOISE TURN-OFF SWITCHING
- SURFACE MOUNT DEVICE

**SMC**

DESCRIPTION

Single high voltage rectifier ranging from 200V to 400 V suited for Switch Mode Power Supplies and other power converters.

ABSOLUTE MAXIMUM RATINGS

| Symbol | Parameter | | Value | Unit |
|--------------------|---|------------------------------------|--------------------------------|----------|
| $I_{F(RMS)}$ | RMS forward current | | 10 | A |
| $I_{F(AV)}$ | Average forward current | $T_J=55^\circ C$ $\delta = 0.5$ | 3 | A |
| I_{FSM} | Non repetitive surge peak forward current | $t_p=10ms$ sinusoidal | 60 | A |
| T_{stg} T_J | Storage and junction temperature range | | - 40 to + 150 - 40 to + 150 | °C °C |

| Symbol | Parameter | | Value | Unit |
|-----------|---------------------------------|--|-------|------|
| V_{RRM} | Repetitive peak reverse voltage | | 400 | V |

THERMAL RESISTANCE

| Symbol | Parameter | | Value | Unit |
|---------------|----------------|--|-------|------|
| $R_{th(j-l)}$ | Junction-leads | | 20 | °C/W |

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ELECTRICAL CHARACTERISTICS STATIC CHARACTERISTICS

| Symbol | Test Conditions | | Min. | Typ. | Max. | Unit |
|----------|---------------------|-----------------|------|------|------|---------|
| V_F * | $T_j = 25^\circ C$ | $I_F = 3 A$ | | | 1.5 | V |
| | $T_j = 100^\circ C$ | | | 1.05 | 1.4 | |
| I_R ** | $T_j = 25^\circ C$ | $V_R = V_{RRM}$ | | | 10 | μA |
| | $T_j = 100^\circ C$ | | | 0.2 | 0.6 | |

Pulse test : * $t_p = 380 \mu s$, duty cycle < 2 %

** $t_p = 5 ms$, duty cycle < 2 %

RECOVERY CHARACTERISTICS

| Symbol | Test Conditions | | Min. | Typ. | Max. | Unit |
|--------|--------------------|--------------|------------------------|------|------|------|
| trr | $T_j = 25^\circ C$ | $I_F = 0.5A$ | $I_{rr} = 0.25A$ | | 25 | ns |
| | | $I_R = 1A$ | | | 60 | |
| | | $I_F = 1A$ | $dI_F/dt = -15A/\mu s$ | | | |
| | | $V_R = 30V$ | | | | |

TURN-OFF SWITCHING CHARACTERISTICS (Without serie inductance)

| Symbol | Test Conditions | | | Min. | Typ. | Max. | Unit |
|-----------|---------------------|------------------------|----------------------|------|------|------|------|
| t_{IRM} | $V_{CC} = 200V$ | $I_F = 3A$ | $L_p \leq 0.05\mu H$ | | 35 | 50 | ns |
| I_{RM} | $T_j = 100^\circ C$ | $dI_F/dt = -50A/\mu s$ | | | 1.5 | 2 | A |

To evaluate the conduction losses use the following equation :

$$P = 1.1 \times I_{F(AV)} + 0.08 \times I_{F(RMS)}^2$$

| | | | |
|-------------|-----|-----|-----|
| Voltage (V) | 200 | 300 | 400 |
| Marking | C2 | C3 | C4 |

Laser marking
Logo indicates cathode

Fig.1 : Low frequency power losses versus average current.

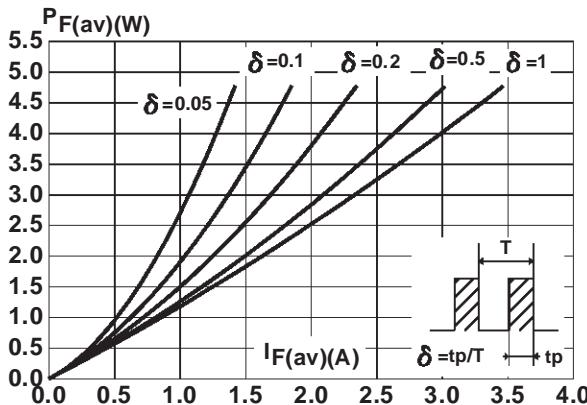


Fig.3 : Non repetitive surge peak forward current versus overload duration.

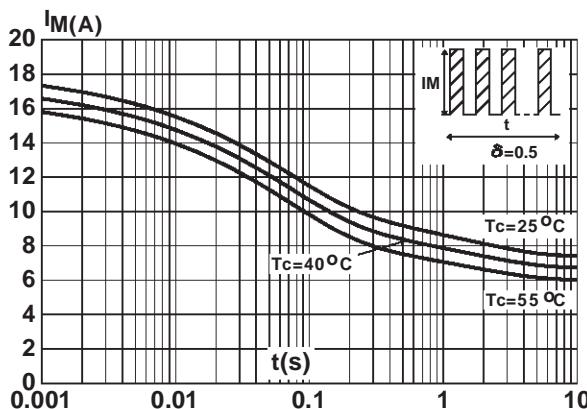


Fig.5 : Voltage drop versus forward current. (Maximum values)

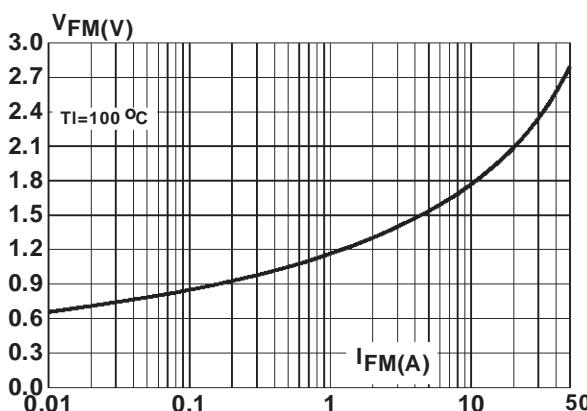


Fig.2 : Peak current versus form factor.

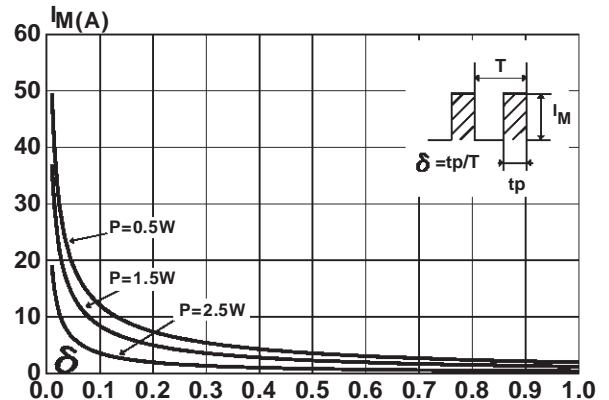


Fig.4 : Relative variation of thermal impedance junction to lead versus pulse duration.

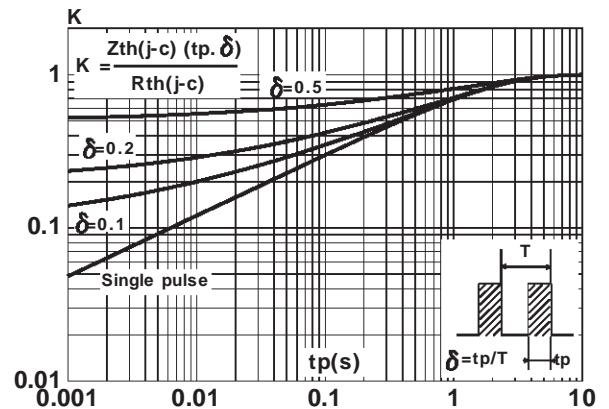
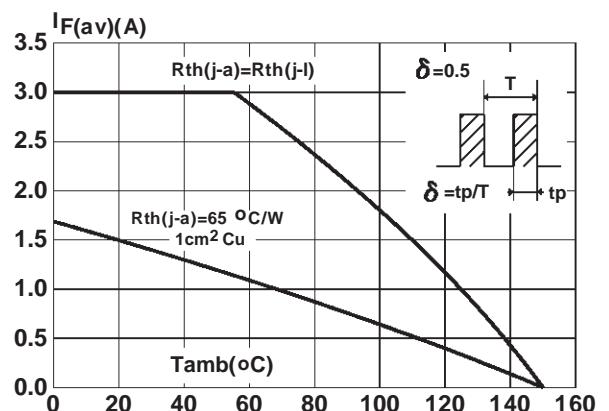


Fig.6 : Average current versus ambient temperature. (duty cycle : 0.5)



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Fig.7 : Recovery time versus dI_F/dt .

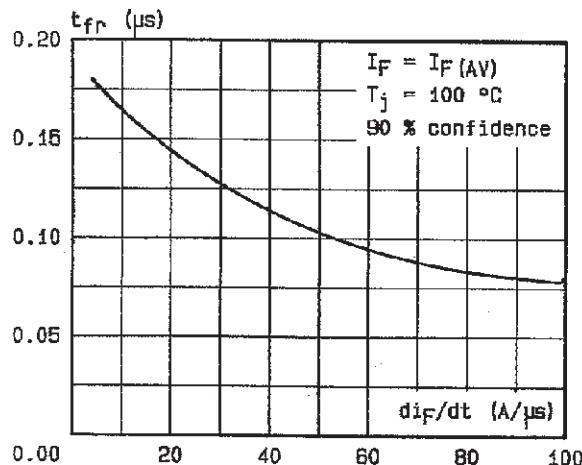


Fig.9 : Peak reverse current versus dI_F/dt .

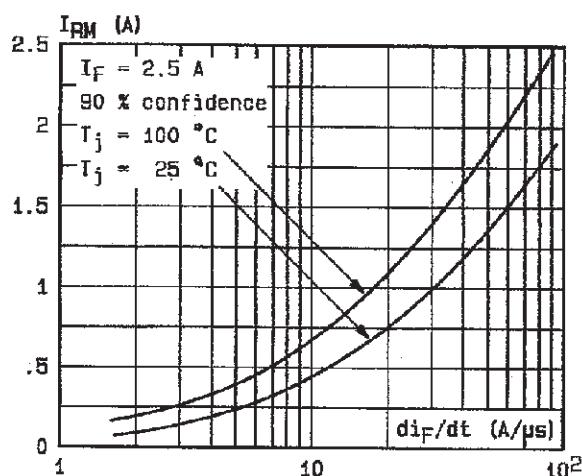


Fig.11 : Dynamic parameters versus junction temperature.

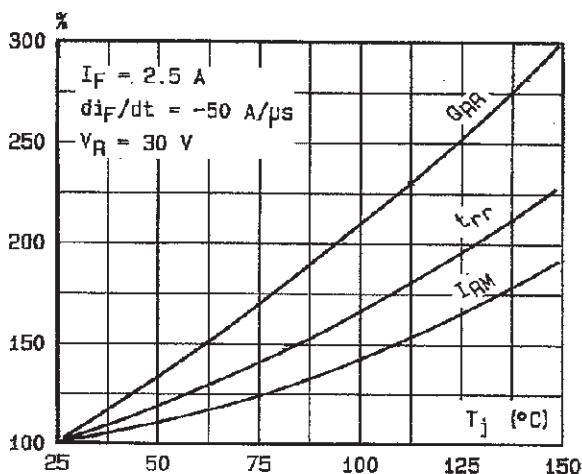


Fig.8 : Peak forward voltage versus dI_F/dt .

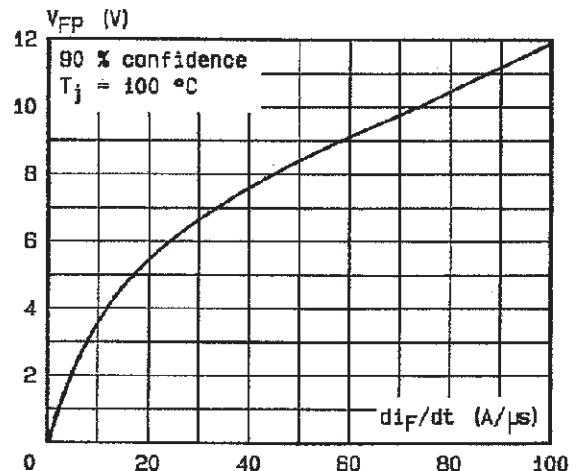


Fig.10 : Recovery charge versus dI_F/dt . (typical values)

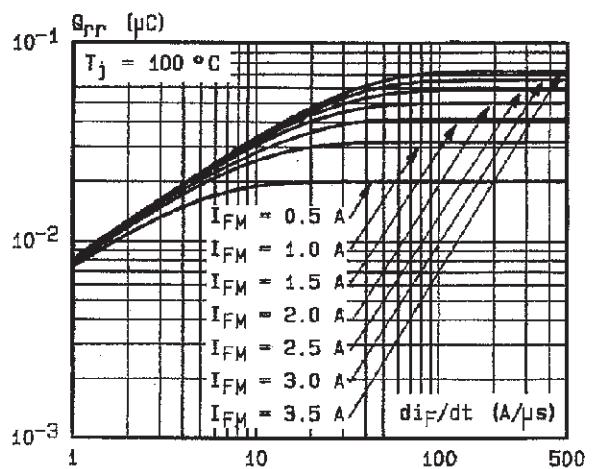
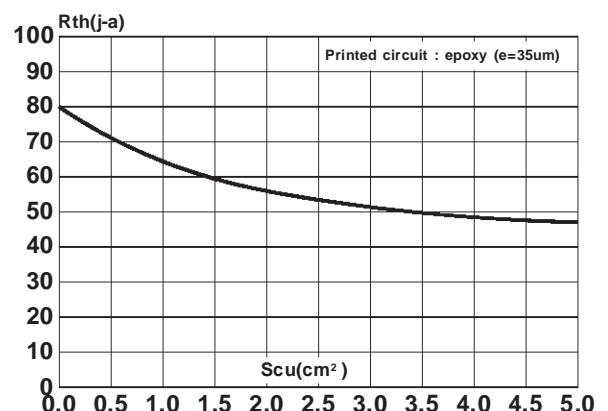


Fig.12 : Thermal resistance junction to ambient versus copper surface under each lead.



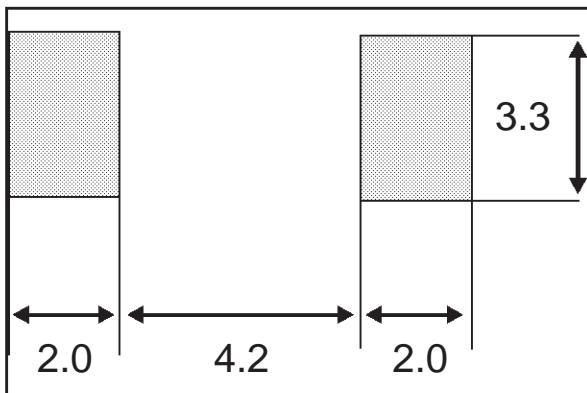
PACKAGE MECHANICAL DATA

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| REF. | DIMENSIONS | | | | | |
|------|-------------|------|------|--------|-------|-------|
| | Millimeters | | | Inches | | |
| | Min. | Typ. | Max. | Min. | Typ. | Max. |
| A1 | 2.40 | 2.70 | 3.00 | 0.094 | 0.106 | 0.118 |
| A2 | 0.05 | | 0.20 | 0.002 | | 0.008 |
| b | 2.90 | | 3.10 | 0.114 | | 0.122 |
| c | 0.29 | | 0.32 | 0.011 | | 0.013 |
| E1 | 6.30 | 6.40 | 6.60 | 0.248 | 0.252 | 0.260 |
| D | 4.80 | 5.00 | 5.20 | 0.189 | 0.197 | 0.205 |
| E | 7.60 | 7.80 | 8.00 | 0.299 | 0.307 | 0.315 |
| L | 1.30 | | 1.70 | 0.051 | | 0.067 |

FOOTPRINT DIMENSIONS

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